TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIV)

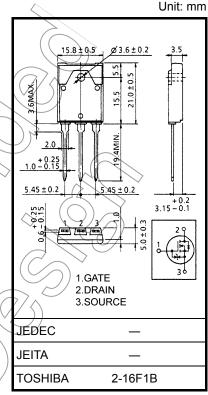
2SK3453

Switching Regulator Applications

- Low drain-source ON-resistance: $R_{DS (ON)} = 0.72 \Omega (typ.)$
- High forward transfer admittance: $|Y_{fS}| = 7.0 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 700 \text{ V)}$
- Enhancement model: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$							
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Characteristics			Symbol	Rating	Unit	
Gate-source voltage	Drain-source voltage			V_{DSS}	700	$(\mathcal{N} \land$	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)			V_{DGR}	700	V	
Drain current Pulse (Note 1) Drain power dissipation (Tc = 25°C) Single pulse avalanche energy (Note 2) Avalanche current Repetitive avalanche energy (Note 3) Channel temperature Pulse (Note 1) IDP 30 W EAS 420 MJ A Tch 10 A Repetitive avalanche energy (Note 3) Channel temperature Tch 150 °C	Gate-source voltage			V_{GSS}	±30	V	
Pulse (Note 1) IDP 30 Drain power dissipation (Tc = 25°C) PD 80 W Single pulse avalanche energy (Note 2) EAS 420 mJ Avalanche current IAR 10 A Repetitive avalanche energy (Note 3) EAR 8 mJ Channel temperature Tch 150 °C	Drain current	DC	(Note 1)	ΙD	10	> ^	
Single pulse avalanche energy (Note 2) Avalanche current Repetitive avalanche energy (Note 3) Channel temperature EAS 420 mJ 10 A Repetitive avalanche energy (Note 3) EAR 8 mJ Channel temperature		Pulse	(Note 1)	I _{DP}	30	V A	
Avalanche current Repetitive avalanche energy (Note 3) Channel temperature (Note 2) Avalanche 2 IAR 10 A B Tch 150 C TCh TCh TCh TCh TCh TCH TCH	Drain power dissipation (Tc = 25°C)			P_{D}	80	W	
Repetitive avalanche energy (Note 3) EAR 8 mJ Channel temperature Tch 150 °C				EAS	420	mJ	
Channel temperature Tch 150 °C	Avalanche current			IAR	10	A	
	Repetitive avalanche energy (Note 3)			EAR)) 8	mJ	
Storage temperature range T _{stg} –55 to 150 °C	Channel temperature			Tch	150	∕ °C	
	Storage temperature range			T _{stg}	-55 to 150	7,¢	



Weight: 5.8 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th} (ch-c)	1.56	°C/W
Thermal resistance, channel to ambient	Rth (ch-a)	41.6	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 7.5 mH, $R_G = 25 \Omega$, $I_{AR} = 10 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

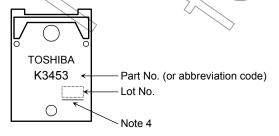
Electrical Characteristics (Ta = 25°C)

Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit		
Gate leakage curr	ent	I _{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА		
Gate-source brea	kdown voltage	V (BR) GSS	$I_G=\pm 10~\mu A,~V_{DS}=0~V$	±30	_	_	V		
Drain cut-OFF cur	rent	I _{DSS}	V _{DS} = 700 V, V _{GS} = 0 V	\	_	100	μА		
Drain-source brea	kdown voltage	V (BR) DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	700	_	_	V		
Gate threshold vo	ltage	V _{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0) >_	4.0	V		
Drain-source ON resistance		R _{DS} (ON)	V _{GS} = 10 V, I _D = 5 A		0.72	1.0	Ω		
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 5 A	4.0	7.0	_	S		
Input capacitance		C _{iss}		\	1700				
Reverse transfer	capacitance	C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	40	_	pF		
Output capacitance		Coss			200				
Switching time F	Rise time	t _r	V _{GS} D D 5 A V _{OUT}	- (40	\rightarrow	<u> </u>		
	Turn-ON time	t _{on}	R _L = 40 Ω		72)	ns		
	Fall time	t _f	Duty ≤ 1%, w = 10 μs		42	_	110		
	Turn-OFF time	t _{off}) —	145	_			
Total gate charge (gate-source plus gate-drain)		Qg		_	53	_			
Gate-source charge		Qgs	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, D = 10 \text{ A}$	_	25	_	nC		
Gate-drain ("miller") charge		Q _{gd} \		_	28	_			

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}		_	_	10	Α
Pulse drain reverse current (Note 1)	IDRP				30	Α
Forward voltage (diode)	V _{DSF}	$I_{DR} = 10 \text{ A}, V_{GS} = 0 \text{ V}$			-1.9	V
Reverse recovery time	\rightarrow t _{rr}	$I_{DR} = 10 \text{ A}, V_{GS} = 0 \text{ V},$		1400		ns
Reverse recovery charge	$\langle \langle Q_{rr} \rangle$	$dI_{DR}/dt = 100 A/\mu s$	_	17.5	_	μС

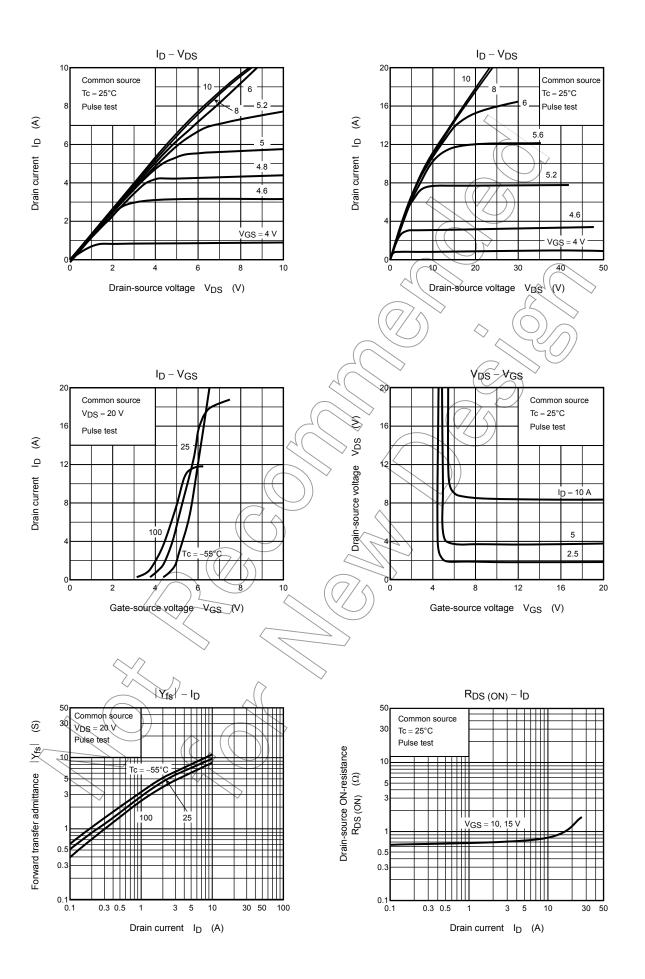
Marking

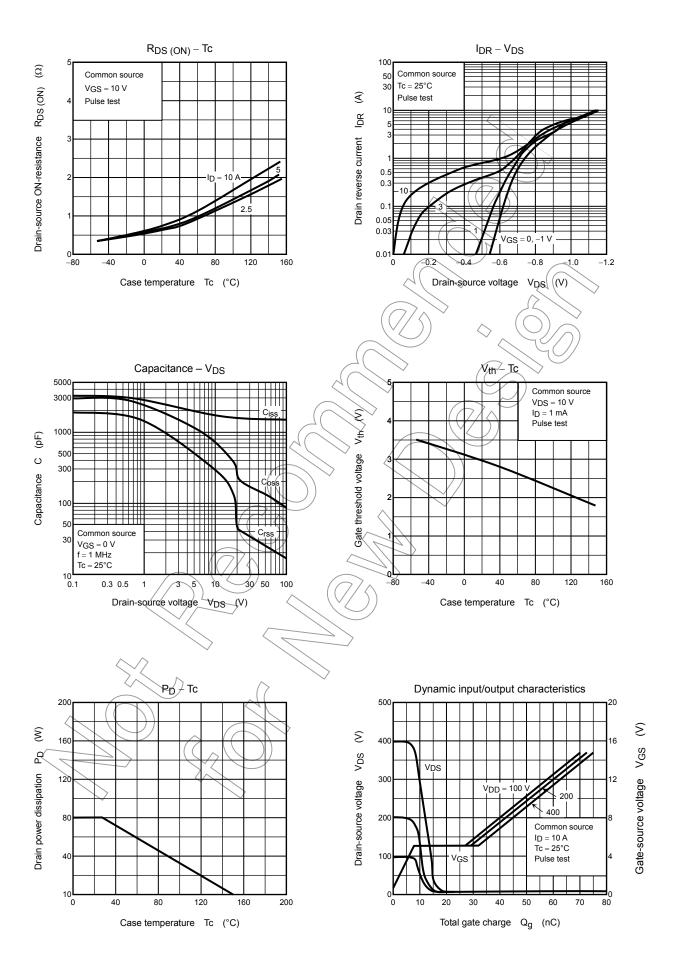


Note 4: A line under a Lot No. identifies the indication of product Labels.

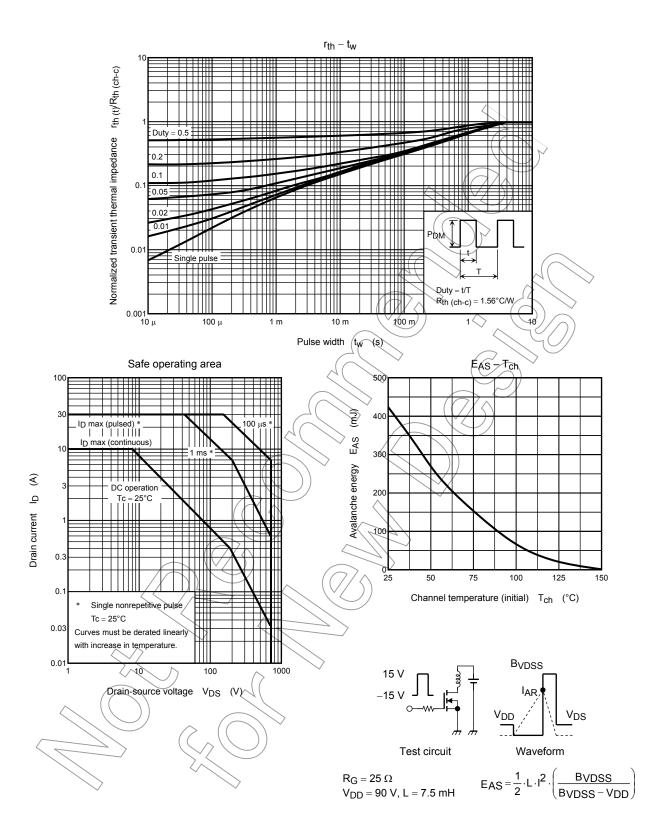
Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.





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